

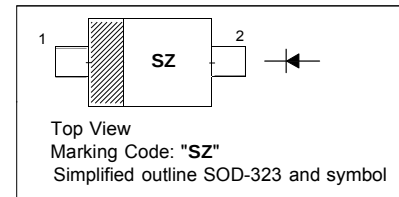
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- Super-high speed switching circuit
- Small current rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Reverse Voltage	V_R	30	V
Average Forward Current	I_O	200	mA
Maximum (Peak) Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current ¹⁾	I_{FSM}	1	A
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

¹⁾ The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	-	0.55	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	50	μA
Terminal Capacitance at $f = 1\text{ MHz}$	C_T	30	-	pF
Reverse Recovery Time at $I_F = I_R = 100\text{ mA}$, $I_{rr} = 10\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}	3	-	ns

